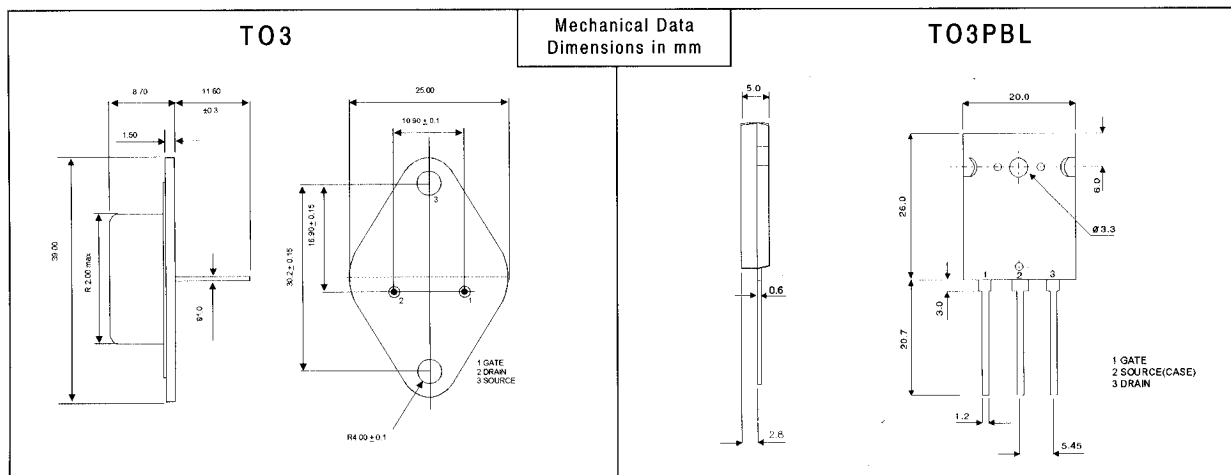




ABSOLUTE MAXIMUM RATING (T case = 25°C unless otherwise stated)		(EC-20)16	(EC-20)20
V _{DSX}	Drain - Source Voltage	160V	200V
V _{GSS}	Gate - Source Voltage	±14V	
I _D	Continuous Drain Current	16A	
I _{D(PK)}	Body Drain Diode	16A	
P _D	Total Power Dissipation @ (T case = 25°C)	250W	
T _{stg}	Storage Temperature Range	-55 to 150°C	
T _j	Maximum Operating Junction Temperature	150°C	
RθJC	Thermal Resistance Junction - case	0.5°C/W	

STATIC CHARACTERISTICS (T case = 25°C unless otherwise stated)

Characteristic		Test Conditions		MIN	TYP	MAX	UNIT
$B V_{DSX}$	Drain - Source Breakdown Voltage	$V_{GS} = -10V$	(EC-20)16	160			V
		$I_D = 10mA$	(EC-20)20	200			V
$B V_{GSS}$	Gate - Source Breakdown Voltage	$V_{DS} = 0$	$I_G = \pm 100\mu A$	± 14			V
$V_{GS(OFF)}$	Gate-Source Cut-Off Voltage	$V_{DS} = 10V$	$I_D = 100mA$	0.10		1.5	V
$V_{DS(SAT)*}$	Drain - Source Saturation Voltage	$V_{GD} = 0$	$I_D = 16A$			12	V
I_{DSX}	Drain - Source Cut - Off Current	$V_{GS} = -10V$	$V_{DS} = 160V$ (EC-20)16			10	mA
			$V_{DS} = 200V$ (EC-20)20			10	
Y_{fs}^*	Forward Transfer Admittance	$V_{DS} = 10V$	$I_D = 3A$	1.4		4	S

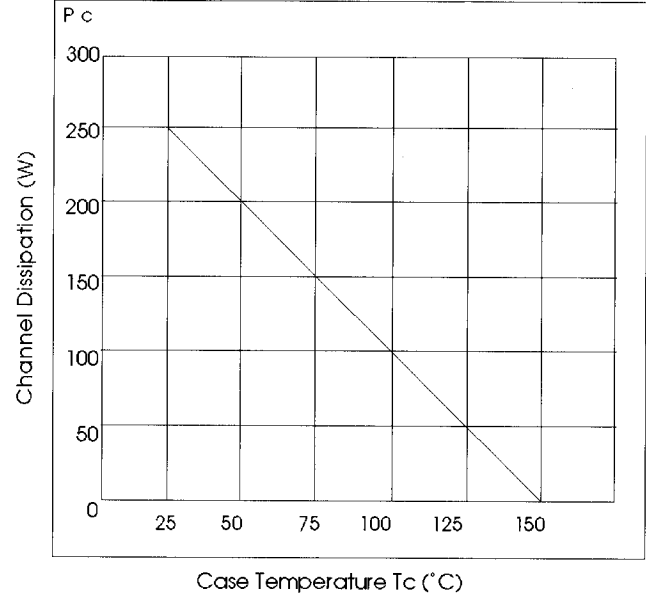
DYNAMIC CHARACTERISTICS (T case = 25°C unless otherwise stated)

Characteristic		Test Conditions	N-Channel	P-Channel	UNIT
C _{iss}	Input Capacitance	V _{DS} = 10V f = 1 MHz	950	1900	pF
C _{oss}	Output Capacitance		550	900	
C _{rss}	Reverse Transfer Capacitance		20	60	
t _{on}	Turn-on Time	V _{DS} = 20V	160	150	ns
t _{off}	Turn-off Time	I _D = 7A	80	110	

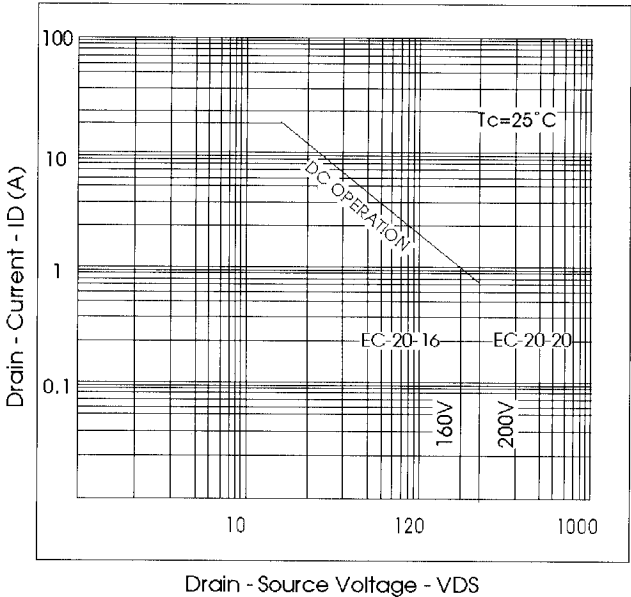
*Pulse Test: Pulse width = 300 μ S, Duty Cycle $\leq$ 2 %

Typical Characteristics for 250W Devices.

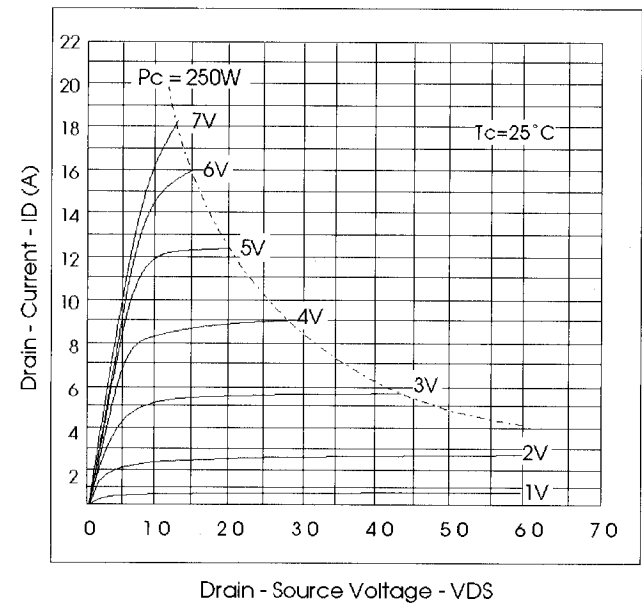
Power vs. Temperature Derating



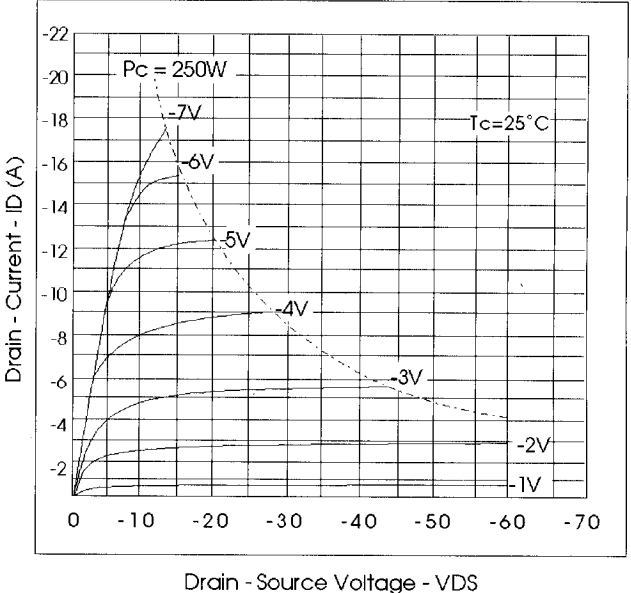
Maximum Safe Operating Area



Typical Output (N-Channel)



Typical Output (P-Channel)



Typical Characteristics for 250W Devices (cont.)

